

## N-channel SiC power MOSFET

$V_{\mathrm{DSS}}$	650V
$R_{DS(on)}(Typ.)$	120m $\Omega$
I <sub>D</sub>	29A
$P_D$	165W

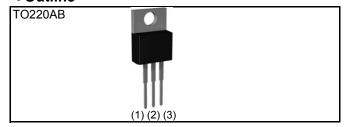
#### Features

- 1) Low on-resistance
- 2) Fast switching speed
- 3) Fast reverse recovery
- 4) Easy to parallel
- 5) Simple to drive
- 6) Pb-free lead plating; RoHS compliant

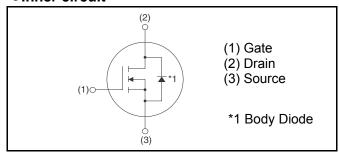
### Application

- Solar inverters
- DC/DC converters
- Switch mode power supplies
- Induction heating
- Motor drives

#### Outline



#### ●Inner circuit



### Packaging specifications

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	Packing	Tube
	Reel size (mm)	-
Typo	Tape width (mm)	-
Туре	Basic ordering unit (pcs)	50
	Packing code	С
	Marking	SCT2120AF

## ● Absolute maximum ratings (T<sub>a</sub> = 25°C)

Parameter		Symbol	Value	Unit
Drain - Source voltage		V <sub>DSS</sub>	650	V
$T_c = 25^{\circ}C$		l <sub>D</sub> *1	29	А
Continuous drain current	T <sub>c</sub> = 100°C	l <sub>D</sub> *1	20	А
Pulsed drain current		I <sub>D,pulse</sub> *2	72	А
Gate - Source voltage (DC)		V <sub>GSS</sub>	-6 to 22	V
Gate - Source surge voltage (T <sub>surge</sub> < 300nsec)		V <sub>GSS-surge</sub> *3	-10 to 26	V
Power dissipation (T <sub>c</sub> = 25°C)		P <sub>D</sub>	165	W
Junction temperature		T <sub>j</sub>	175	°C
Range of storage temperature		T <sub>stg</sub>	-55 to +175	°C

### ●Thermal resistance

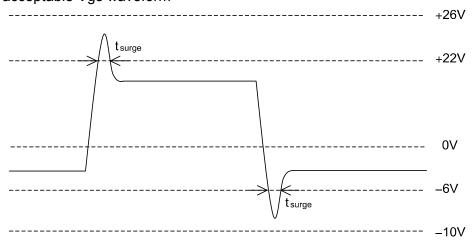
Parameter	Symbol	Values			Unit
r arameter	Gymbol	Min.	Тур.	Max.	Offic
Thermal resistance, junction - case	$R_{thJC}$	-	0.70	0.91	°C/W
Soldering temperature, wavesoldering for 10s	$T_{sold}$	-	-	265	°C

## ●Electrical characteristics (T<sub>a</sub> = 25°C)

Parameter	Symbol	Conditions	Values			Unit
r arameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V$ , $I_D = 1mA$	650	-	-	V
Zero gate voltage drain current	I <sub>DSS</sub>	$V_{DS} = 650V, V_{GS} = 0V$ $T_{j} = 25^{\circ}C$ $T_{j} = 150^{\circ}C$		1 2	10	μА
Gate - Source leakage current	I <sub>GSS+</sub>	$V_{GS} = +22V, V_{DS} = 0V$	-	-	100	nA
Gate - Source leakage current	I <sub>GSS-</sub>	$V_{GS} = -6V, V_{DS} = 0V$	-	-	-100	nA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 3.3 \text{mA}$	1.6	2.8	4.0	V

<sup>\*1</sup> Limited only by maximum temperature allowed.

<sup>\*3</sup> Example of acceptable Vgs waveform



\*4 Pulsed

<sup>\*2</sup> PW  $\leq$  10  $\mu s,$  Duty cycle  $\leq$  1%

# ●Electrical characteristics (T<sub>a</sub> = 25°C)

Parameter	Cymbol	Conditions		Values		Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
		$V_{GS} = 18V, I_D = 10A$				
Static drain - source on - state resistance	R <sub>DS(on)</sub> *4	T <sub>j</sub> = 25°C	-	120	156	mΩ
		T <sub>j</sub> = 125°C	-	149	-	
Gate input resistance	$R_G$	f = 1MHz, open drain	-	13.8	-	Ω
Transconductance	g <sub>fs</sub> *4	$V_{DS} = 10V, I_{D} = 10A$	-	2.7	-	S
Input capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0V	-	1200	-	
Output capacitance	C <sub>oss</sub>	V <sub>DS</sub> = 500V	-	90	-	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1MHz	-	13	-	
Effective output capacitance, energy related	C <sub>o(er)</sub>	$V_{GS} = 0V$ $V_{DS} = 0V$ to 300V	-	115	-	pF
Turn - on delay time	t <sub>d(on)</sub> *4	$V_{DD} = 300V, I_{D} = 10A$	-	22	-	
Rise time	t <sub>r</sub> *4	V <sub>GS</sub> = 18V/0V	-	31	-	20
Turn - off delay time	t <sub>d(off)</sub> *4	$R_L = 30\Omega$	-	60	-	ns
Fall time	t <sub>f</sub> *4	$R_G = 0\Omega$	-	19	-	
Turn - on switching loss	E <sub>on</sub> *4	$V_{DD} = 300V, I_{D} = 10A$ $V_{GS} = 18V/0V$ $R_{G} = 0\Omega, L = 500\mu H$	-	61	-	1
Turn - off switching loss	E <sub>off</sub> *4	*E <sub>on</sub> includes diode reverse recovery	-	41	-	μJ

# ●Gate Charge characteristics (T<sub>a</sub> = 25°C)

Parameter	Symbol	Conditions	Values			Unit
Farameter	Syllibol	Conditions	Min.	Тур.	Max.	Offic
Total gate charge	$Q_g^{*4}$	V <sub>DD</sub> = 300V	-	61	-	
Gate - Source charge	Q <sub>gs</sub> *4	I <sub>D</sub> = 10A	-	14	-	nC
Gate - Drain charge	Q <sub>gd</sub> *4	V <sub>GS</sub> = 18V	-	21	-	
Gate plateau voltage	V <sub>(plateau)</sub>	$V_{DD} = 300V, I_D = 10A$	-	10.4	-	V

## ●Body diode electrical characteristics (Source-Drain) (T<sub>a</sub> = 25°C)

Parameter	Symbol	Conditions	Values			Unit
r ai ai ii etei	Syllibol	Conditions	Min.	Тур.	Max.	Offic
Inverse diode continuous, forward current	l <sub>S</sub> *1	T <sub>c</sub> = 25°C	ı	-	29	А
Inverse diode direct current, pulsed	I <sub>SM</sub> *2	-1 <sub>c</sub> = 25°C	1	-	72	Α
Forward voltage	V <sub>SD</sub> *4	V <sub>GS</sub> = 0V, I <sub>S</sub> = 10A	-	4.3	-	V
Reverse recovery time	t <sub>rr</sub> *4		-	33	-	ns
Reverse recovery charge	Q <sub>rr</sub> *4	$I_F = 10A, V_R = 400V$ di/dt = 160A/ $\mu$ s	-	53	-	nC
Peak reverse recovery current	I <sub>rrm</sub> *4		-	3.0	-	Α

## ● Typical Transient Thermal Characteristics

Symbol	Value	Unit
R <sub>th1</sub>	96.1m	
R <sub>th2</sub>	404m	K/W
R <sub>th3</sub>	196m	

Symbol	Value	Unit
C <sub>th1</sub>	1.55m	
C <sub>th2</sub>	5.23m	Ws/K
C <sub>th3</sub>	83.3m	

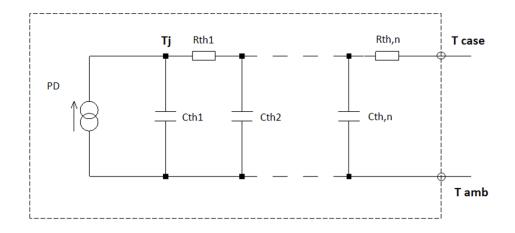


Fig.1 Power Dissipation Derating Curve

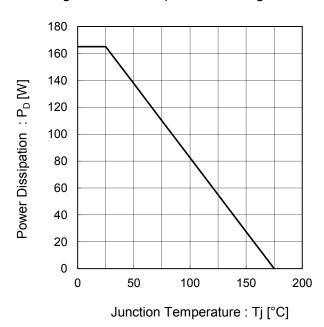
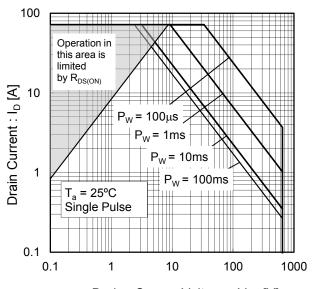


Fig.2 Maximum Safe Operating Area



Drain - Source Voltage :  $V_{DS}$  [V]

Fig.3 Typical Transient Thermal Resistance vs. Pulse Width

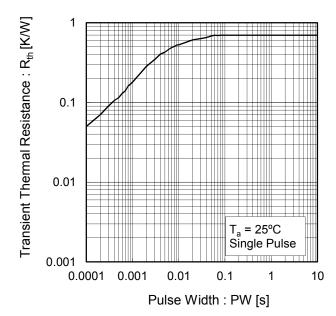


Fig.4 Typical Output Characteristics(I)

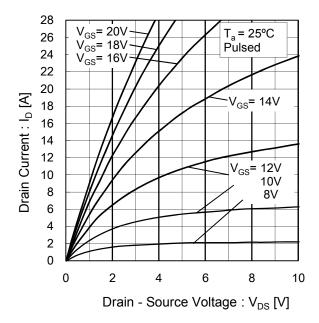


Fig.5 Typical Output Characteristics(II)

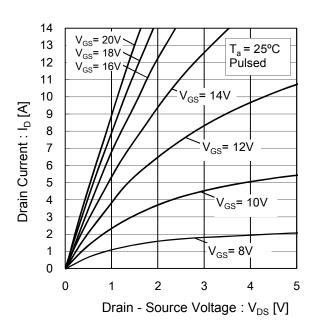


Fig.6  $T_j$  = 150°C Typical Output Characteristics(I)

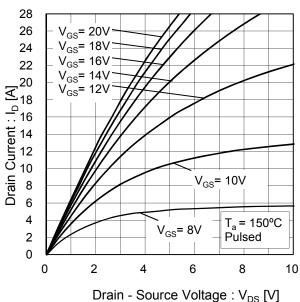
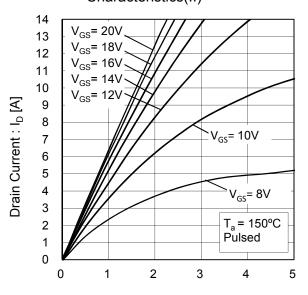
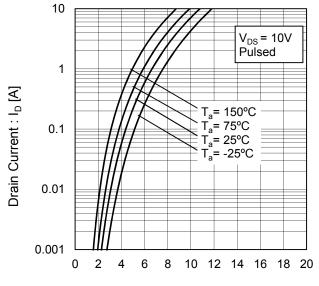


Fig.7 T<sub>j</sub> = 150°C Typical Output Characteristics(II)



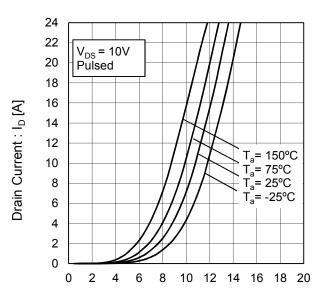
Drain - Source Voltage : V<sub>DS</sub> [V]

Fig.8 Typical Transfer Characteristics (I)



Gate - Source Voltage : V<sub>GS</sub> [V]

Fig.9 Typical Transfer Characteristics (II)



Gate - Source Voltage : V<sub>GS</sub> [V]

Fig.10 Gate Threshold Voltage vs. Junction Temperature

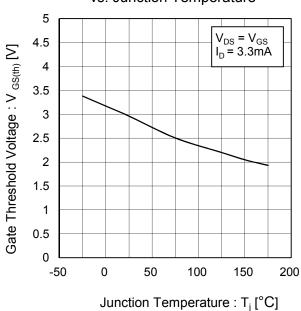
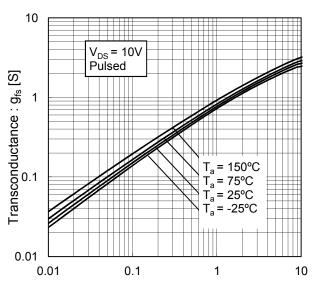
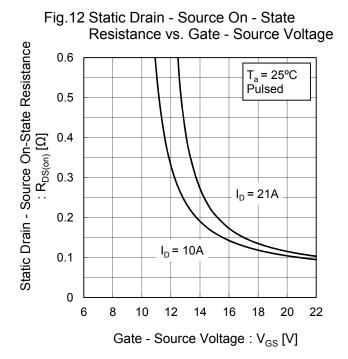


Fig.11 Transconductance vs. Drain Current



Drain Current : I<sub>D</sub> [A]



Resistance vs. Junction Temperature Static Drain - Source On-State Resistance 0.3 V<sub>GS</sub> = 18V Pulsed 0.25  $:R_{DS(on)}\left[ \Omega \right]$ 0.2 I<sub>D</sub> = 20A 0.15 I<sub>D</sub> = 10A 0.1 0.05 0 -50 0 200 50 100 150 Junction Temperature : T<sub>i</sub> [°C]

Fig.13 Static Drain - Source On - State

Fig.14 Static Drain - Source On - State Resistance vs. Drain Current Static Drain - Source On-State Resistance 1 V<sub>GS</sub> = 18V Pulsed  $:R_{\mathsf{DS}(\mathsf{on})}\left[ \Omega \right]$ T<sub>a</sub> = 150°C = 125°C 75°C  $T_a = 25^{\circ}C$  $T_a = -25^{\circ}C$ 0.1 0.1 1 100 10 Drain Current: ID [A]

Fig.15 Typical Capacitance

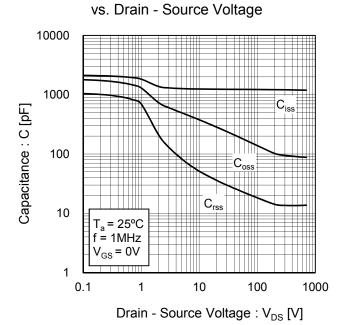
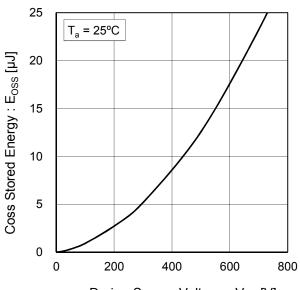


Fig.16 Coss Stored Energy



Drain - Source Voltage : V<sub>DS</sub> [V]

Fig.17 Switching Characteristics

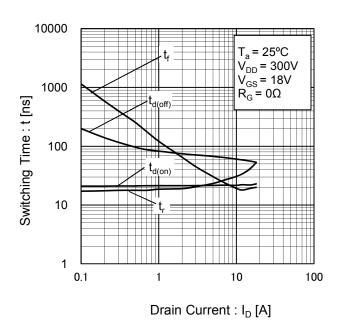
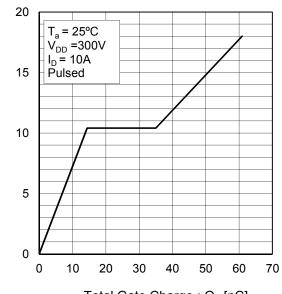


Fig.18 Dynamic Input Characteristics



Gate - Source Voltage :  $V_{GS}$  [V]

Fig.19 Typical Switching Loss vs. Drain - Source Voltage

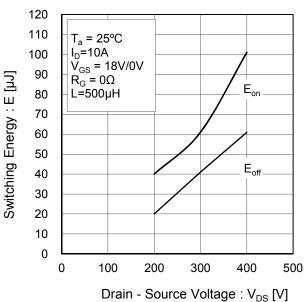


Fig.20 Typical Switching Loss vs. Drain Current

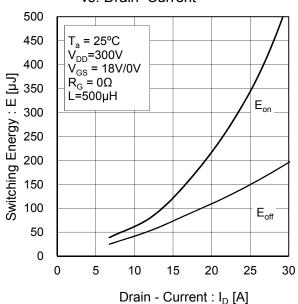
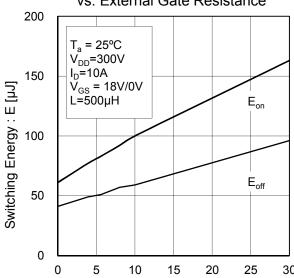


Fig.21 Typical Switching Loss vs. External Gate Resistance



External Gate Resistance :  $R_G [\Omega]$ 

Fig.22 Inverse Diode Forward Current vs. Source - Drain Voltage

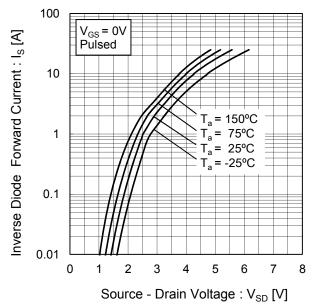
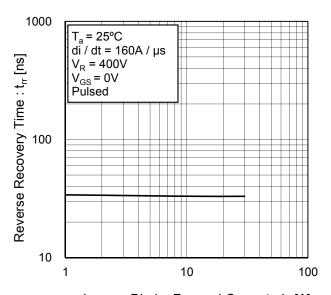


Fig.23 Reverse Recovery Time vs.Inverse Diode Forward Current



Inverse Diode Forward Current :  $I_S$  [A]

#### Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

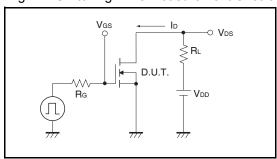


Fig.2-1 Gate Charge Measurement Circuit

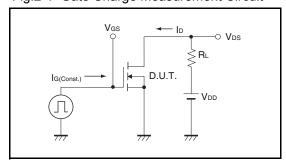


Fig.3-1 Switching Energy Measurement Circuit

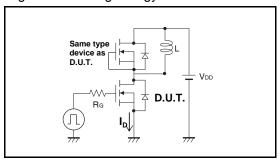


Fig.4-1 Reverse Recovery Time Measurement Circuit Fig.4-2 Reverse Recovery Waveform

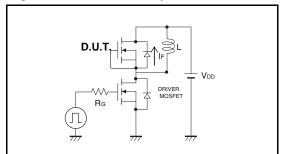


Fig.1-2 Switching Waveforms

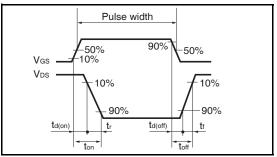


Fig.2-2 Gate Charge Waveform

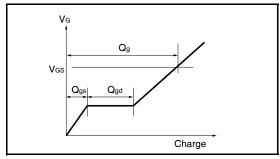
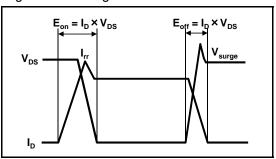
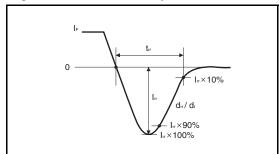


Fig.3-2 Switching Waveforms





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